

INJ0203AC1-T150

High Speed Switching
Silicon P-channel MOSFET

AEC-Q101 Compliance

DESCRIPTION

INJ0203AC1 is a Silicon P-channel MOSFET.

This product is most suitable for use such as portable machinery, because of low voltage drive and low on resistance.

FEATURE

- Input impedance is high, and not necessary to consider a drive electric current.

- V_{th} is low, and drive by low voltage is possible.

$V_{th} = -0.4 \sim -1.2V$

- Low on Resistance. $R_{DS(on)} = 100m\Omega$ (TYP).

- High speed switching.

- Small package for easy mounting.

APPLICATION

Switching

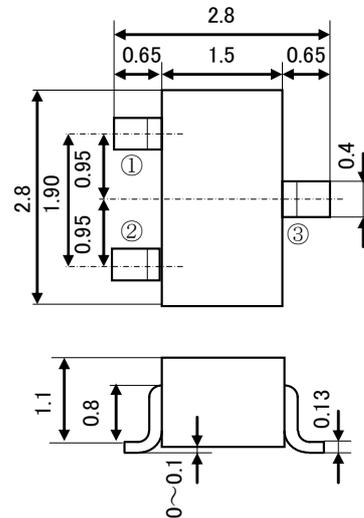
MAXIMUM RATINGS ($T_a = 25^\circ C$)

Symbol	Parameter	Rating	Unit
V_{DSS}	Drain-Source Voltage	-20	V
V_{GSS}	Gate-Source Voltage	-10	V
I_D	Drain Current(DC)	-2	A
I_{DP}	Drain current(Pulse) ※1	-4	A
P_D	Total Power Dissipation	200	mW
T_{ch}	Channel Temperature	+150	$^\circ C$
T_{stg}	Storage Temperature	-55~+150	$^\circ C$

※1: $P_w \leq 10 \mu s$, Duty cycle $\leq 1\%$

OUTLINE DRAWING

Unit: mm



JEITA: SC-59

JEDEC: Similar to TO-236

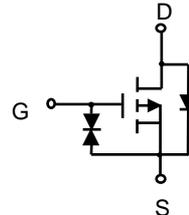
TERMINAL CONNECTER

①: GATE

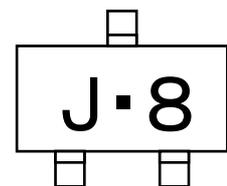
②: SOURCE

③: DRAIN

EQUIVALENT CIRCUIT



MARKING



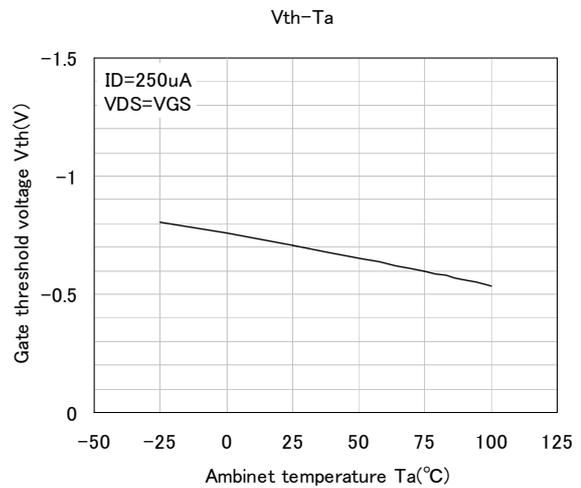
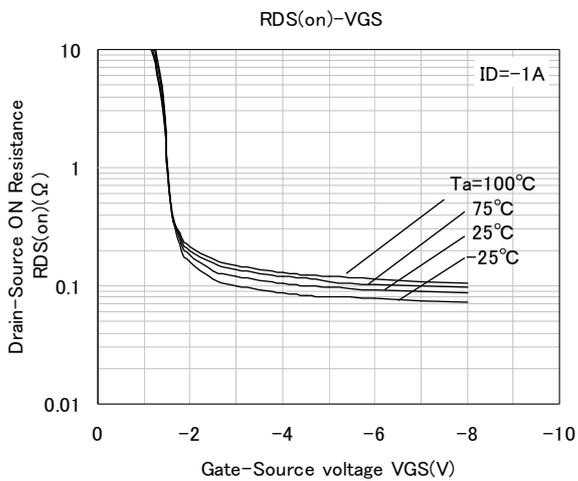
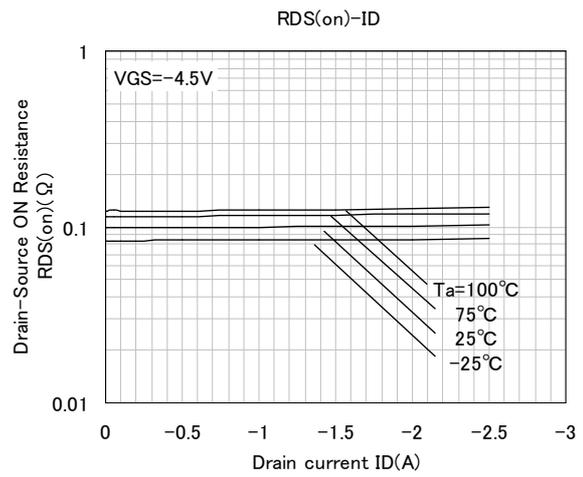
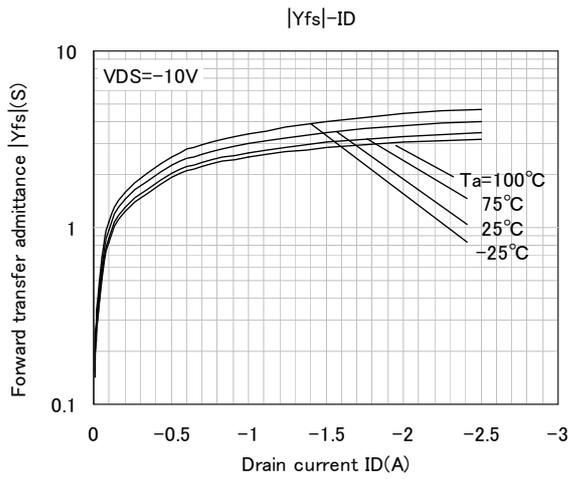
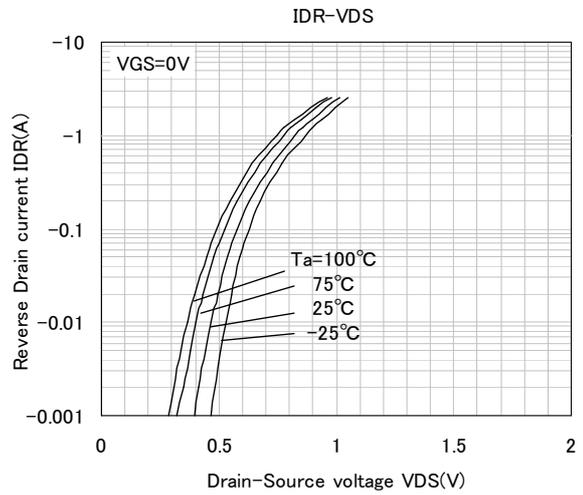
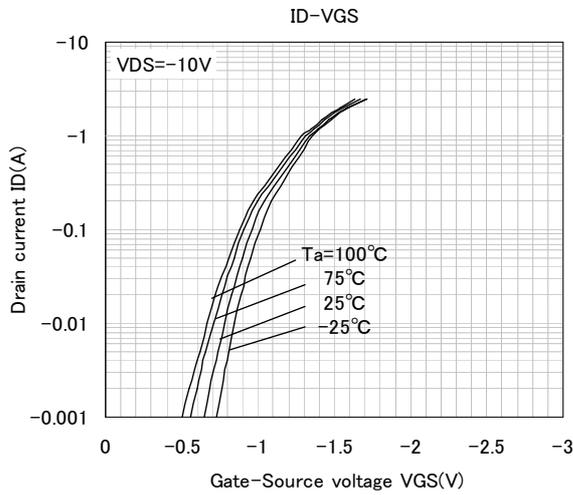
ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

Parameter	Symbol	Test Condition	Limit			Unit
			MIN	TYP	MAX	
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -100 \mu A, V_{GS} = 0V$	-20	-	-	V
Gate-Source Leak current	I_{GSS}	$V_{GS} = \pm 10V, I_{DS} = 0A$	-	-	± 10	μA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -20V, V_{GS} = 0V$	-	-	-10	μA
Gate Threshold Voltage	V_{th}	$I_D = -250 \mu A, V_{DS} = V_{GS}$	-0.4	-	-1.2	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = -10V, I_D = -1A$	-	3.0	-	S
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$I_D = -1A, V_{GS} = -4.5V$	-	100	-	$m\Omega$
Input Capacitance	C_{iss}	$V_{DS} = -10V, V_{GS} = 0V, f = 1MHz$	-	340	-	pF
Output Capacitance	C_{oss}		-	90	-	pF
Switching Time	t_{on}	$V_{DD} = -15V, I_D = -1A$	-	30	-	ns
	t_{off}	$V_{GS} = 0 \sim -10V$	-	130	-	ns

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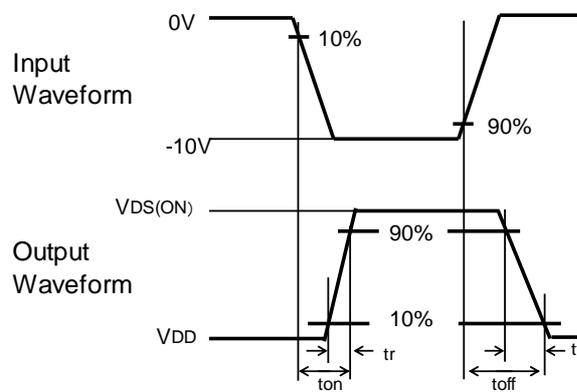
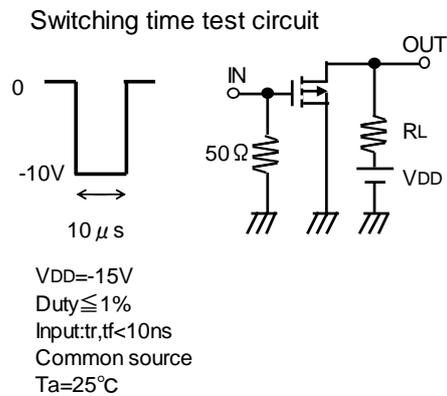
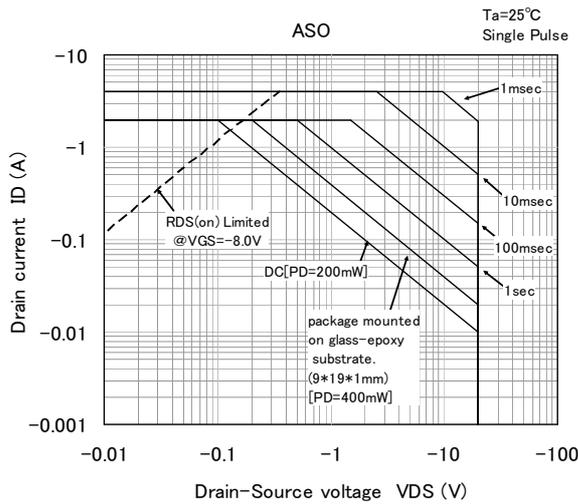
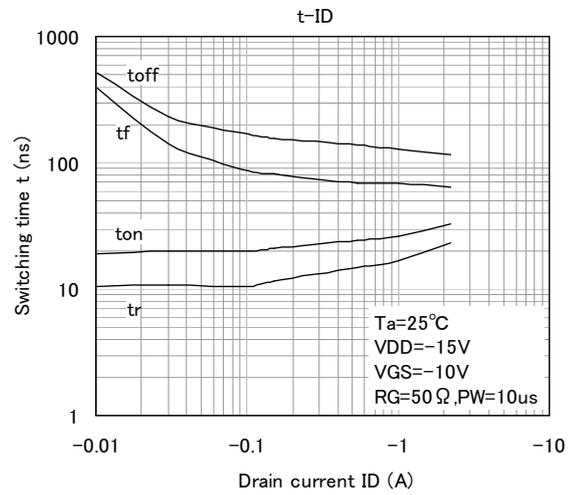
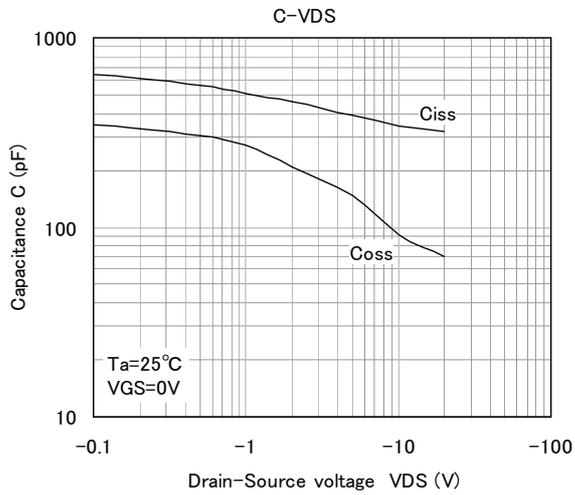
TYPICAL CHARACTERISTICS



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TYPICAL CHARACTERISTICS





Keep safety first in your circuit designs!

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